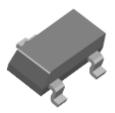
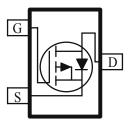
## P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY				
<b>V</b> <sub>DS</sub> (V)	r <sub>DS(on)</sub> (OHM)	<b>ID</b> (A)		
-20	$0.079 @V_{CS} = -4.5V$	-1.7		
	$0.110@V_{CS} = -2.5V$	-1.5		





ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Maximum	Units			
Drain-Source Voltage			-20	v		
Gate-Source Voltage			±8	v		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	T_	-1.7			
	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	цD	-1.4	Α		
ulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-2.5			
Continuous Source Current (Diode Conduction) <sup>a</sup>			±0.28	Α		
Den Dississtin <sup>a</sup>	$T_A=25^{\circ}C$	D.	0.34	W		
Power Dissipation <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	тD	0.22	vv		
Operating Junction and Storage Temperature Range		TJ, Tstg	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
	$t \ll 5 \sec$	D	375	<sup>0</sup> CM1		
Maximum Junction-to-Ambient <sup>a</sup>	Steady-State	R <sub>THJA</sub>	430	Ċw		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

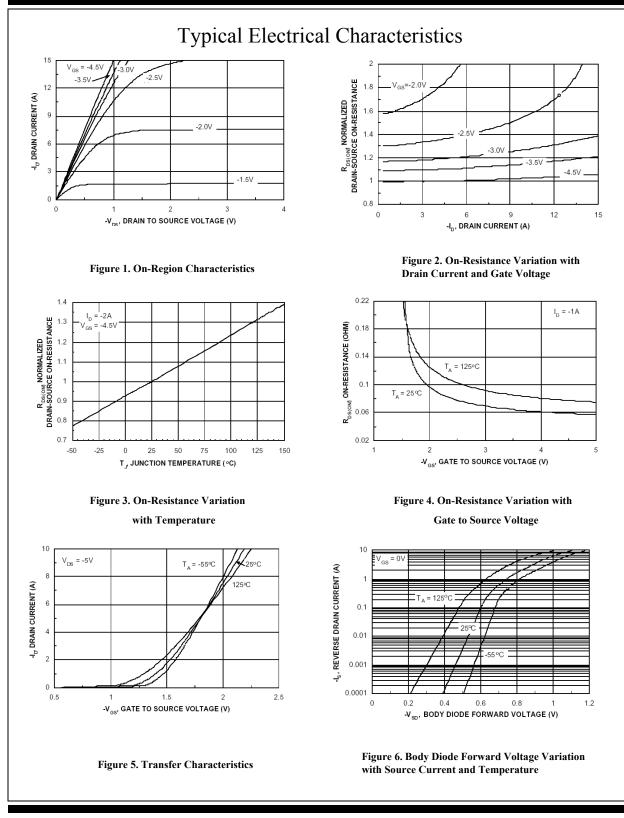
SPECIFICATIONS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Conditions	Limits			11.4	
Parameter	Symbol	Test Conditions	Min	Min Typ Ma		unit x	
Static						-	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \text{ uA}$	-0.4			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -16 V, V_{GS} = 0 V$			-1		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10	uA	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = -5 V, V_{GS} = -4.5 V$	-5			Α	
Drain-Source On-Resistance <sup>A</sup>	T	$V_{GS} = -4.5 \text{ V}, I_D = -1.7 \text{ A}$			79	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A}$			110		
Forward Tranconductance <sup>A</sup>	$g_{\rm fs}$	$V_{DS} = -5 V$ , $I_D = -1.25 A$		9		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_{S} = -0.46 \text{ A}, V_{GS} = 0 \text{ V}$		-0.65		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	$V_{DS} = -10 V$ , $V_{GS} = -4.5 V$ ,		7.2			
Gate-Source Charge	Q <sub>gs</sub>	$v_{\rm DS} = -10  v,  v_{\rm GS} = -4.3  v,$ $I_{\rm D} = -1.7  {\rm A}$		1.7		nC	
Gate-Drain Charge	Q <sub>gd</sub>	$I_{\rm D} = -1.7$ A		1.5			
Turn-On Delay Time	t <sub>d(on)</sub>			10			
Rise Time	t <sub>r</sub>	$V_{DD} = -10 \text{ V}, \text{ I}_{L} = -1 \text{ A},$		9		ne	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = -4.5 \text{ V}, R_G = 6 \Omega$		27		ns	
Fall-Time	t <sub>f</sub>			11			

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Repetitive rating, pulse width limited by junction temperature.

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## Freescale



f = 1 MHz V<sub>GS</sub> = 0 V

20

15

#### **Typical Electrical Characteristics** 1000 = -3.5A -5\ I, 10V 68, GATE-SOURCE VOLTAGE (V) Ciss 800 15 CAPACITANCE (pF) 3 600 2 400 Coss 1 200 7 0 0 0 2 8 1 3 4 5 6 7 9 0 5 10 Q d GATE CHARGE (nC) -VDS, DRAIN TO SOURCE VOLTAGE (V) Figure 7. Gate Charge Characteristic Figure 8. Capacitance Characteristic 100 5 LIMIT R<sub>DS(ON)</sub> 100µs 4

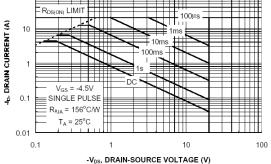
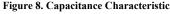
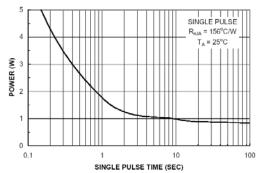
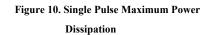
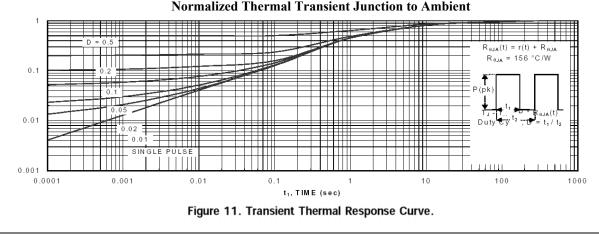


Figure 9. Maximum Safe Operating Area





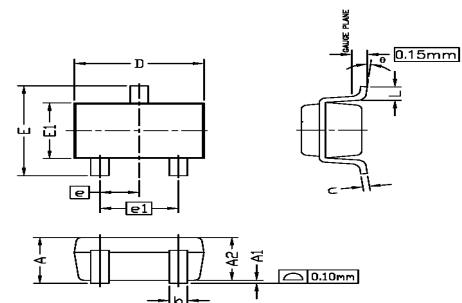




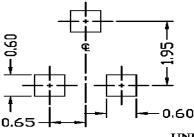
Normalized Thermal Transient Junction to Ambient

# Package Information

SC70 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



ma more	SYMBOLS DIMENSIONS IN MILLIMBTERS		DIMENSIONS IN INCHES					
SIMBOLS	MIN	NOM	MAX	MIN	NOM	MAX		
Α			1.10			0.043		
A1	0.00		0.10	0.00		0.004		
A2	0.7	0.9	1.00	0.028	0.035	0.039		
ь	0.15		0.30	0.006		0.012		
C	0.08		0.22	0.003		0.009		
D	1.85	2,10	2,15	0.073	0.083	0.085		
Е	1.80	2.30	2.40	0.071	0.091	0.094		
e	0.65 BSC				0.091 0.094 0.026 BSC			
el	1.30 BSC				0.051 BSC	.091 0.094 6 BSC		
<b>E</b> 1	1.1	1.30	1.4	0.043	0.051	0.055		
L	0.26	0.36	0.46	0.010	0.014	0.018		
Ð	0°	4°	8°	0°	4°	80		

UNIT: mm

### NOTE

- 1. ALL DIMENSIONS ARE IN MILLMETERS.
- 2. DIMENSIONS ARE INCLUSIVE OF PLATING.
- 3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 3 MILS EACH.
- 4. DIE IS FACING UP FOR MOLD AND FACING DOWN FOR TRIM/FORM. ie:REVERSE TRIM/FORM.
- 5. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 6. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.